

## Cascadable Silicon Bipolar MMIC Amplifier

# Technical Data

#### **MSA-0385**

#### Features

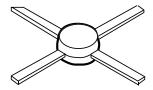
- Cascadable 50  $\Omega$  Gain Block
- **3 dB Bandwidth:** DC to 2.5 GHz
- 12.0 dB Typical Gain at 1.0 GHz
- \* 10.0 dBm Typical  $P_{1 dB}$  at 1.0 GHz
- Unconditionally Stable (k>1)
- Low Cost Plastic Package

#### Description

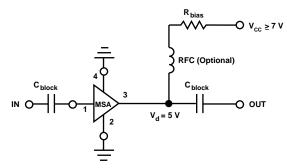
The MSA-0385 is a high performance silicon bipolar Monolithic Microwave Integrated Circuit (MMIC) housed in a low cost plastic package. This MMIC is designed for use as a general purpose  $50 \Omega$  gain block. Typical applications include narrow and broad band IF and RF amplifiers in commercial and industrial applications.

The MSA-series is fabricated using HP's 10 GHz f<sub>T</sub>, 25 GHz f<sub>MAX</sub>, silicon bipolar MMIC process which uses nitride self-alignment, ion implantation, and gold metallization to achieve excellent performance, uniformity and reliability. The use of an external bias resistor for temperature and current stability also allows bias flexibility.

#### **85 Plastic Package**



#### **Typical Biasing Configuration**



#### MSA-0385 Absolute Maximum Ratings

Parameter	Absolute Maximum <sup>[1]</sup>
Device Current	70 mA
Power Dissipation <sup>[2,3]</sup>	400 mW
RF Input Power	+13dBm
Junction Temperature	150°C
Storage Temperature	−65 to 150°C

Thermal Resistance<sup>[2,4]</sup>:

 $\theta_{\rm jc} = 105^{\circ} {\rm C/W}$ 

#### Notes:

- 1. Permanent damage may occur if any of these limits are exceeded.
- 2.  $T_{CASE} = 25$ °C.
- 3. Derate at 9.5 mW/°C for  $T_C > 108$ °C.

4. See MEASUREMENTS section "Thermal Resistance" for more information.

Symbol	Parameters and Test Conditions: $I_d$ = 35 mA, $Z_0$ = 50 $\Omega$		Units	Min.	Тур.	Max.
GP	Power Gain $( \mathbf{S}_{21} ^2)$	f = 0.1  GHz	dB		12.5	
		$f = 1.0 \mathrm{GHz}$		10.0	12.0	
$\Delta G_P$	Gain Flatness	f = 0.1  to  1.6  GHz	dB		$\pm 0.7$	
$f_{3dB}$	3 dB Bandwidth		GHz		2.5	
VSWR	Input VSWR	f = 0.1  to  3.0  GHz			1.5:1	
	Output VSWR	f = 0.1  to  3.0  GHz			1.7:1	
NF	$50 \Omega$ Noise Figure	f = 1.0  GHz	dB		6.0	
$P_{1\;dB}$	Output Power at 1 dB Gain Compression	f = 1.0 GHz	dBm		10.0	
$IP_3$	Third Order Intercept Point	f = 1.0 GHz	dBm		23.0	
tD	Group Delay	f = 1.0  GHz	psec		125	
Vd	Device Voltage		V	4.0	5.0	6.0
dV/dT	Device Voltage Temperature Coefficient		mV/°C		-8.0	

### Electrical Specifications<sup>[1]</sup>, $T_A = 25^{\circ}C$

Note:

1. The recommended operating current range for this device is 20 to 50 mA. Typical performance as a function of current is on the following page.

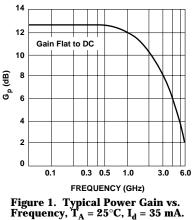
 $S_{21}$  $S_{11}$  $S_{12}$  $S_{22}$ Freq. GHz Mag Ang dB Mag Ang dB Mag Ang Mag Ang 178 12.6 4.26 175 -18.1.124 2-10 0.1 .09 .13 0.2 12.54.24 170 -18.4.120 3 -20 .09 171 .13 12.4 -18.40.4 .08 166 4.17 161 .121 6 .14 -41 8 0.6 .07 160 12.34.10 151-18.0.126 -57.15 -710.8 .07 15512.14.01 142-17.9.127 12 .16 1.0 .06 15211.93.92 133 -17.6.132 12 .18 -84 .05 -1693.63 -16.518 .21 -1121.511.2112.1492.0 .08 -17410.4 3.29 92 -15.6.167 19 .23 -1362.5.12 -1732.9879 -14.6.186 22 .25 -1509.5 3.0 .20 178 8.4 2.6463 -14.1.198 20 .26 -1663.5 .25 170 7.52.3647 -13.5.211 17 .25 -1744.0 .28 160 6.5 2.1233 -13.0.207 13 .24 -1805.0.42 134 4.7 1.71 7 -12.2.224 .20 168 4 -7 6.0 .50 99 2.71.37 -18-12.0.252 .23 133

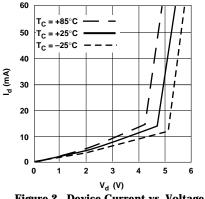
MSA-0385 Typical Scattering Parameters ( $Z_0 = 50 \Omega$ ,  $T_A = 25^{\circ}C$ ,  $I_d = 35 mA$ )

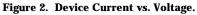
A model for this device is available in the DEVICE MODELS section.

#### Typical Performance, $T_A = 25^{\circ}C$

(unless otherwise noted)







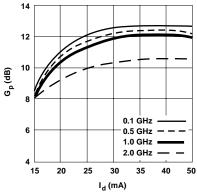


Figure 3. Power Gain vs. Current.

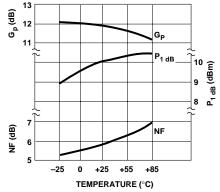


Figure 4. Output Power at 1 dB Gain Compression, NF and Power Gain vs. Case Temperature, f = 1.0 GHz, I<sub>d</sub>=35mA.

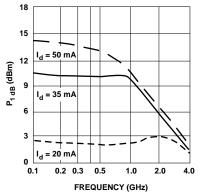


Figure 5. Output Power at 1 dB Gain **Compression vs. Frequency.** 

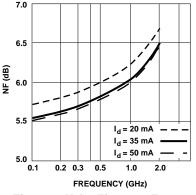
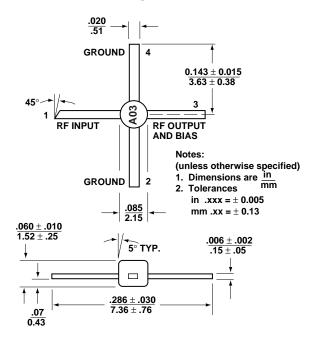


Figure 6. Noise Figure vs. Frequency.



### **85 Plastic Package Dimensions**